

## **isc Silicon NPN Power Transistors**

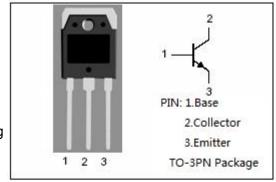
**TIP54** 

### **DESCRIPTION**

- DC Current Gain -h<sub>FE</sub> = 30~150@ I<sub>C</sub>= 0.3A
- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub> = 400V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

• Designed for line operated audio output amplifier, and switching power supply drivers applications.

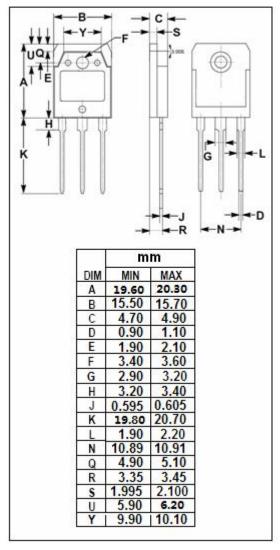


# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	3.0	А
Ісм	Collector Current-Peak	5.0	А
lв	Base Current	0.6	А
P <sub>D</sub>	Collector Power Dissipation T <sub>C</sub> =25 °C 100		W
T <sub>j</sub>	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$ C

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.25	°C/W



isc website: www.iscsemi.com

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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	400		V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 10V		1.5	٧
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V; I <sub>E</sub> = 0		1.0	mA
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 300V; I <sub>B</sub> = 0		1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.3A; V <sub>CE</sub> = 10V	30	150	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 10V	10		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 10V	2.5		MHz

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